

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

- 1-2. (Canceled)
3. (New) A semiconductor device comprising:
 - a semiconductor chip having electrodes;
 - a stress relieving layer provided on the semiconductor chip so as to avoid at least a part of each of the electrodes;
 - wiring formed from one of the electrodes over the stress relieving layer, at least a portion of the wiring over the stress relieving layer having a width narrower than a width of each of the electrodes; and
 - external electrodes formed on the wiring over the stress relieving layer.
4. (New) The semiconductor device of claim 3, the wiring being formed of any one selected from a group consisting of aluminum, aluminum alloy, chromium, a layer of copper or gold, two layers of copper and gold, two layers of chromium and copper, two layers of chromium and gold, two layers of platinum and gold, and three layers of chromium, copper and gold.
5. (New) The semiconductor device of claim 3, the wiring being formed of a chromium layer over the stress relieving layer and a layer of at least one of copper and gold.
6. (New) The semiconductor device of claim 3, the wiring including a titanium layer.
7. (New) The semiconductor device of claim 6, the wiring having one of a layer of nickel formed over the titanium layer and two layers of platinum and gold.
8. (New) The semiconductor device of claim 3, further comprising a protective film on a surface of the semiconductor chip opposite to a surface having the electrodes.

9. (New) The semiconductor device of claim 8, the protective film being of a material different from a material used for the semiconductor chip, and having a melting point not less than a melting point of solder.

10. (New) The semiconductor device of claim 3, further comprising a radiator on a surface of the semiconductor chip opposite to a surface having the electrodes.

11. (New) The semiconductor device of claim 3, the stress relieving layer having a sloping end portion, and a portion of the wiring on the sloping end portion has a width narrower than a width of each of the electrodes.

12. (New) The semiconductor device of claim 3, a portion the wiring on the one of the electrodes having a width greater than a width of each of the electrodes.

13. (New) The semiconductor device of claim 3, further comprising a passivation film on the semiconductor chip and under the stress relieving layer, the wiring having a first portion on the passivation film between the one of the electrodes and the stress relieving layer, the wiring having a second portion extending from the first portion and formed on the stress relieving layer.